Abstracts

New Development Trends for Silicon RF Device Technologies

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Today more than ever, low cost, high performance RF devices are in high demand due to explosive growth in the wireless communications business. As the RF performance of silicon-based technologies improve, silicon solutions are an obvious choice due to its low cost, high reliability and the ability to integrate other analog and logic functions on-chip. This paper will highlight some of the development efforts that are taking place to improve silicon device technologies for RF and microwave applications. Performance of current state-of-the-art silicon bipolar, MOSFET, TFSOI and SiGe HBTs will be discussed.

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